IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of Art Unit: 2814) Shunpei YAMAZAKI Examiner: N. Ngo) Serial No. 09/499,619 **CERTIFICATE OF MAILING** Filed: February 7, 2000 I hereby certify that this correspondence is being deposited with The United States Postal Service with sufficient postage as First **ELECTRO-OPTICAL DEVICE**

Class Mail in an envelope addressed to: Commissioner for Patents, Washington, D.C. 2023 1 on 1510 / Le (0)

Washington, D.C. 20231, on

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents Washington, DC 20231

AND METHOD FOR

MANUFACTURING THE SAME)

Sir:

In accordance with the provisions of 37 C.F.R. 1.56 and 37 C.F.R. 1.97-1.99, Applicant submits herewith a Form PTO-1449 listing references known to Applicant and requests that these references be considered by the Examiner and made of record in the above identified application. Copies of the references listed are submitted herewith in accordance with 37 C.F.R. 1.98(a).

U.S. Patent 4,942,441 is in the family of JP 62-229873.

JP 01-272146 was cited by the Japanese Patent Office for asserting that in an active matrix liquid crystal device, it would have been easy to use a P-channel thin film transistor and an N-channel thin film transistor connected to each other through a transparent conductive film.

JP 02-216129, JP 03-255425, Japan Utility Model Laid Open No. 03-081922 and Japan Utility Model Laid Open No. 03-071382 were cited by the Japanese Patent Office for asserting that in a well known active matrix liquid crystal display device, it was well know to connect another IC by a COG method or a TAB method.

The Integrated Circuit Engineering (1) article was cited by the Japanese Patent Office for showing it is well known that an N-channel MOS transistor is capable of driving at a higher speed since it uses electrons as carriers.

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The Integrated Circuit Engineering (2) article was cited by the Japanese Patent Office for showing that a circuit constituted with complementary MOS transistors is formed by using a plurality of MOS transistors having a same channel type.

JP 57-100467 and 56-059291 were previously submitted with English abstracts and full translations are submitted herewith.

U.S. Patent 4,655,551 submitted herewith may relate to the use of a flexible substrate. The Examiner's attention is also particularly directed to JP 2-251992, of record with a full English translation. The Examiner is requested to carefully consider this reference in connection with the Amendment filed May 15, 2002.

This Information Disclosure Statement is being filed concurrently with a Request for Continued Examination (RCE), therefore no fee is believed to be required.

The Commissioner is hereby authorized to charge any fees connected with this filing which may be required now, or credit any overpayment to Deposit Account No. 50-2280.

Respectfully submitted,

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